

## Supplementary Information

### Optical simulation of ultimate performance enhancement in ultrathin Si solar cells by semiconductor nanocrystal energy transfer sensitization

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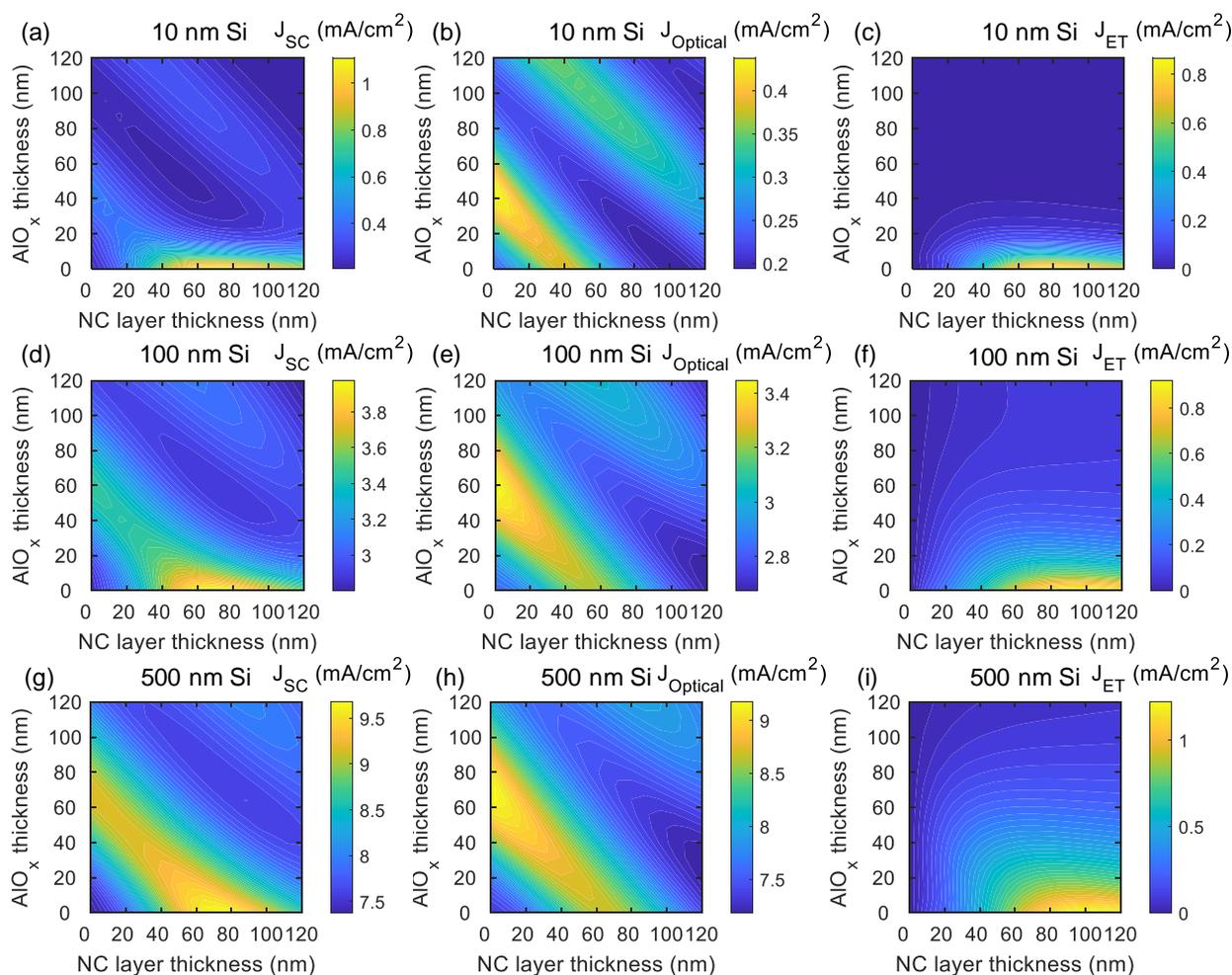


Fig. S1. Calculated contour plots of  $J_{SC}$ , and contributions of  $J_{Optical}$  and  $J_{ET}$  for NC-sensitized ultrathin Si with metallic back contact with 100% reflectivity for Si thicknesses of: (b-c) 10 nm; (d-f) 100 nm, and (g-i) 500 nm, under AM1.5G 1 Sun solar irradiation.